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Vishay Siliconix

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET



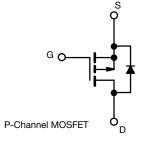
TO-263
S
Top View G

#### **FEATURES**

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R<sub>q</sub> and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



PRODUCT SUMMARY		
V <sub>DS</sub> (V)	-40	
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0051	
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0071	
I <sub>D</sub> (A)	-100	
Configuration	Single	
Package	TO-263	



ABSOLUTE MAXIMUM RATINGS (	T <sub>C</sub> = 25 °C, unles	s otherwise noted	)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		$V_{DS}$	-40	V
Gate-source voltage		$V_{GS}$	± 20	V
Continuous drain current	$T_C = 25  ^{\circ}C^{a}$	I <sub>D</sub>	-100	
Continuous drain current	T <sub>C</sub> = 125 °C	чD	-72	
Continuous source current (diode conduction) a	Continuous source current (diode conduction) a		-100	Α
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	-300	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-41	
Single pulse avalanche energy	L = 0.1 IIII1	E <sub>AS</sub>	84	mJ
Maximum power dissipation <sup>b</sup>	er dissipation b $T_C = 25 ^{\circ}C$	150	W	
waxiinuin powei dissipation -	T <sub>C</sub> = 125 °C	r D	50	VV
Operating junction and storage temperature ran	ige	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	$R_{thJA}$	40	°C/W
Junction-to-case (drain)		$R_{thJC}$	1	C/VV

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static		•			•		·
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = -250 μA	-40	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.5	-	-2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V	-	-	-1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 125 °C	-	-	-50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 175 °C	-	-	-250	
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \le -5 \text{ V}$	-50	-	-	Α
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -30 A	-	0.0042	0.0051	
Drain actures on state registeres a	Б	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -30 A, T <sub>J</sub> = 125 °C	-	-	0.0079	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -30 A, T <sub>J</sub> = 175 °C	-	-	0.0094	Ω
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -25 A	-	0.0059	0.0071	071
Forward transconductance a	9fs	V <sub>DS</sub> =	-15 V, I <sub>D</sub> = -30 A	-	103	-	S
Dynamic <sup>b</sup>							•
Input capacitance	C <sub>iss</sub>			-	11 063	14 500	
Output capacitance	Coss	$V_{GS} = 0 V$	$V_{DS} = -25 \text{ V, f} = 1 \text{ MHz}$	-	847	1110	pF
Reverse transfer capacitance	C <sub>rss</sub>	7		-	757	1000	
Total gate charge <sup>c</sup>	$Q_g$			-	185	280	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -10 V	$V_{DS} = -20 \text{ V}, I_{D} = -50 \text{ A}$	-	25	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>	7		-	30	-	
Gate resistance	$R_g$		f = 1 MHz	1.8	3.6	5.4	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	15	25	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = -20 V, $R_L$ = 0.4 Ω - 180 $I_D$ $\cong$ -50 A, $V_{GEN}$ = -10 V, $R_g$ = 1 Ω - 145		280			
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			220	ns		
Fall time <sup>c</sup>	t <sub>f</sub>	7		-	160	250	1
Source-Drain Diode Ratings and Char	acteristics b						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-300	А
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = -30 A, V <sub>GS</sub> = 00.84 -1		-1.5	V		

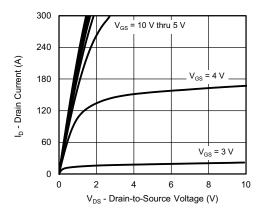
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

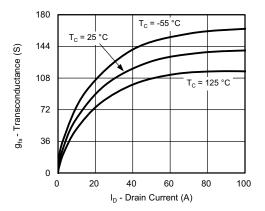
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



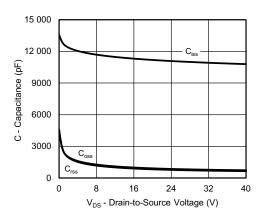
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



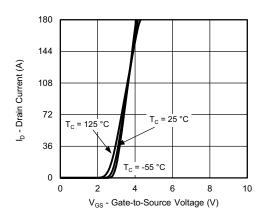
#### **Output Characteristics**



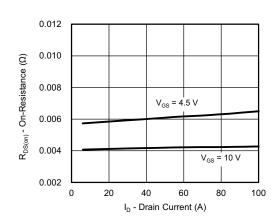
Transconductance



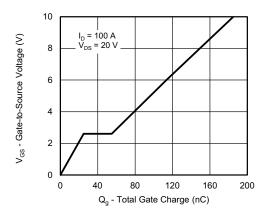
Capacitance



**Transfer Characteristics** 



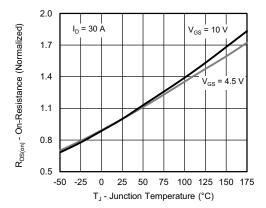
On-Resistance vs. Drain Current



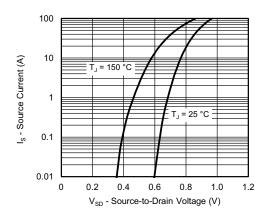
Gate Charge



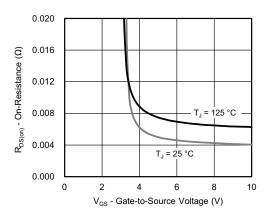
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



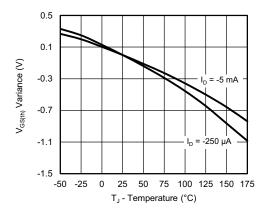
On-Resistance vs. Junction Temperature



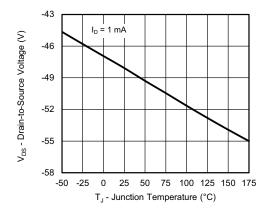
**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to-Source Voltage



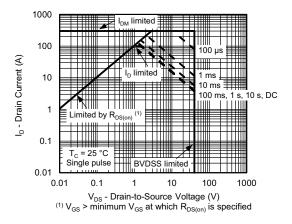
Threshold Voltage



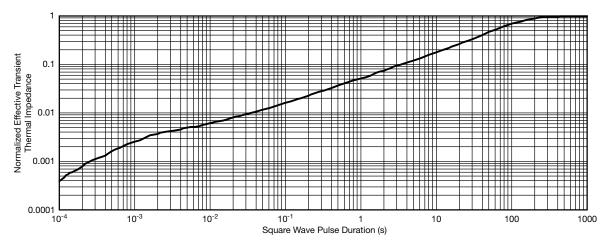
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



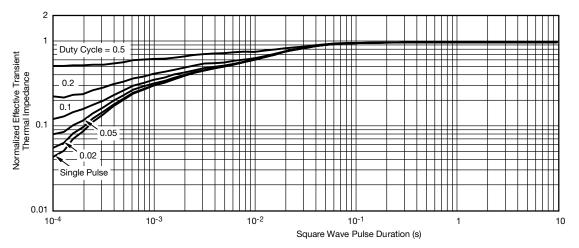
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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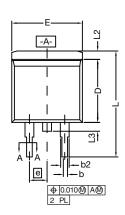
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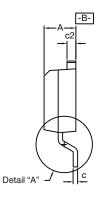


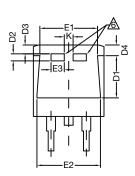
# TO-263 (D<sup>2</sup>PAK): 3-LEAD

#### **VERSION 1: FACILITY CODE = T**

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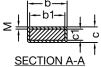








**DETAIL A (ROTATED 90°)** 



<u>_</u>	b	1	<u> </u>
< T		10	ပ
SI	FCTION	1 A-A	Ŧ

#### **Notes**

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

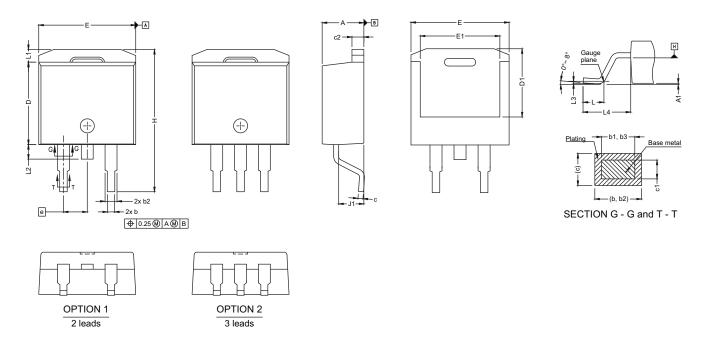
		INCHES		MILLIN	METERS
	DIM.	MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	E	0.380	0.410	9.652	10.414
	<u>E1</u>	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100	) BSC	2.54	BSC
K		0.045	0.055	1.143	1.397
	L	0.575	0.625	14.605	15.875
	L1	0.090	0.110	2.286	2.794
	L2	0.040	0.055	1.016	1.397
	L3	0.050	0.070	1.270	1.778
	L4	0.010	BSC	0.254	BSC
	М	-	0.002	-	0.050



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### **VERSION 2: FACILITY CODE = N**



DIM.	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.70	0.90
b1	0.51	0.89
b2	1.20	1.46
b3	1.17	1.37
С	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.60	9.00
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
е	2.54	BSC
Н	15.0	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25	5 typ.
L4	4.78	5.28
J1	2.56	2.96

DWG: 5843





## RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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